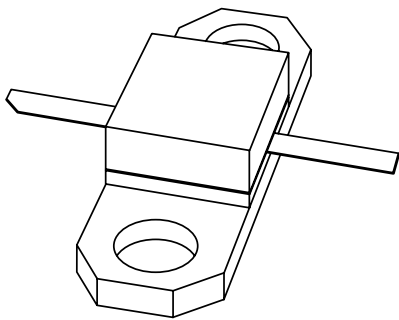


DATA SHEET



LLE18010X NPN microwave power transistor

Product specification
Supersedes data of December 1994

1999 Apr 22

NPN microwave power transistor

LLE18010X

FEATURES

- Diffused emitter ballasting resistors providing excellent current sharing and withstanding a high VSWR
- Interdigitated structure provides high emitter efficiency
- Gold metallization realizes very good stability of the characteristics and excellent lifetime
- Multicell geometry gives good balance of dissipated power and low thermal resistance
- Internal input prematching ensures good stability and allows an easier design of wideband circuits.

APPLICATION

Intended for use in common emitter, class AB amplifiers in CW conditions for professional applications up to 2 GHz.

DESCRIPTION

NPN silicon planar epitaxial microwave power transistor in a SOT437A glued cap metal ceramic flange package, with emitter connected to flange.

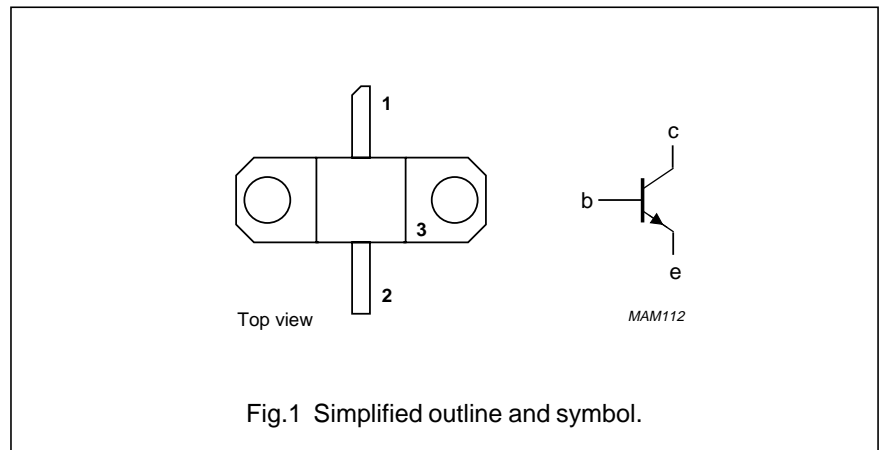
QUICK REFERENCE DATA

Microwave performance up to $T_{mb} = 25\text{ }^{\circ}\text{C}$ in a common emitter class AB amplifier.

MODE OF OPERATION	f (GHz)	V _{CE} (V)	I _{CQ} (mA)	P _{L1} (W)	G _{po} (dB)	Z _i ; Z _L (Ω)
Class AB (CW)	1.85	24	10	≥1	≥8.5	see Figs 6 and 7

PINNING - SOT437A

PIN	DESCRIPTION
1	collector
2	base
3	emitter connected to flange



WARNING

Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO slab is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	40	V
V _{CER}	collector-emitter voltage	R _{BE} = 220 Ω	–	30	V
V _{CEO}	collector-emitter voltage	open base	–	15	V
V _{EBO}	emitter-base voltage	open collector	–	3	V
I _C	collector current (DC)		–	250	mA
P _{tot}	total power dissipation	T _{mb} = 75 °C	–	4.5	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	200	°C
T _{slid}	soldering temperature	t ≤ 10 s; note 1	–	235	°C

Note

- Up to 0.2 mm from ceramic.

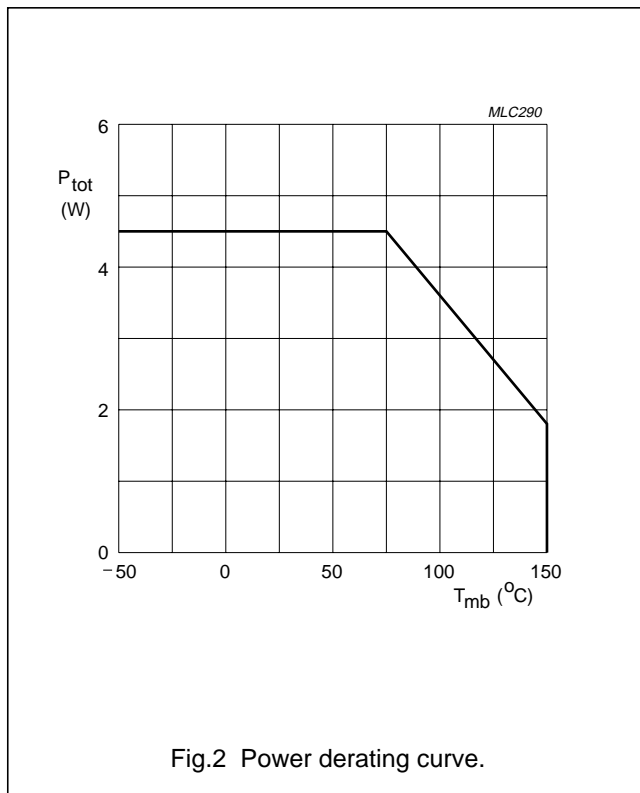


Fig.2 Power derating curve.

NPN microwave power transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	$T_j = 100\text{ °C}$	22	K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink		0.2	K/W

CHARACTERISTICS

$T_{mb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 20\text{ V}$	–	11	μA
$V_{(BR)CER}$	collector-emitter breakdown voltage	$I_C = 1\text{ mA}; R_{BE} = 220\ \Omega$	30	–	V
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 1\text{ mA}$	40	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 0.5\text{ mA}$	3	–	V
h_{FE}	DC current gain	$I_C = 125\text{ mA}; V_{CE} = 5\text{ V}$	15	150	

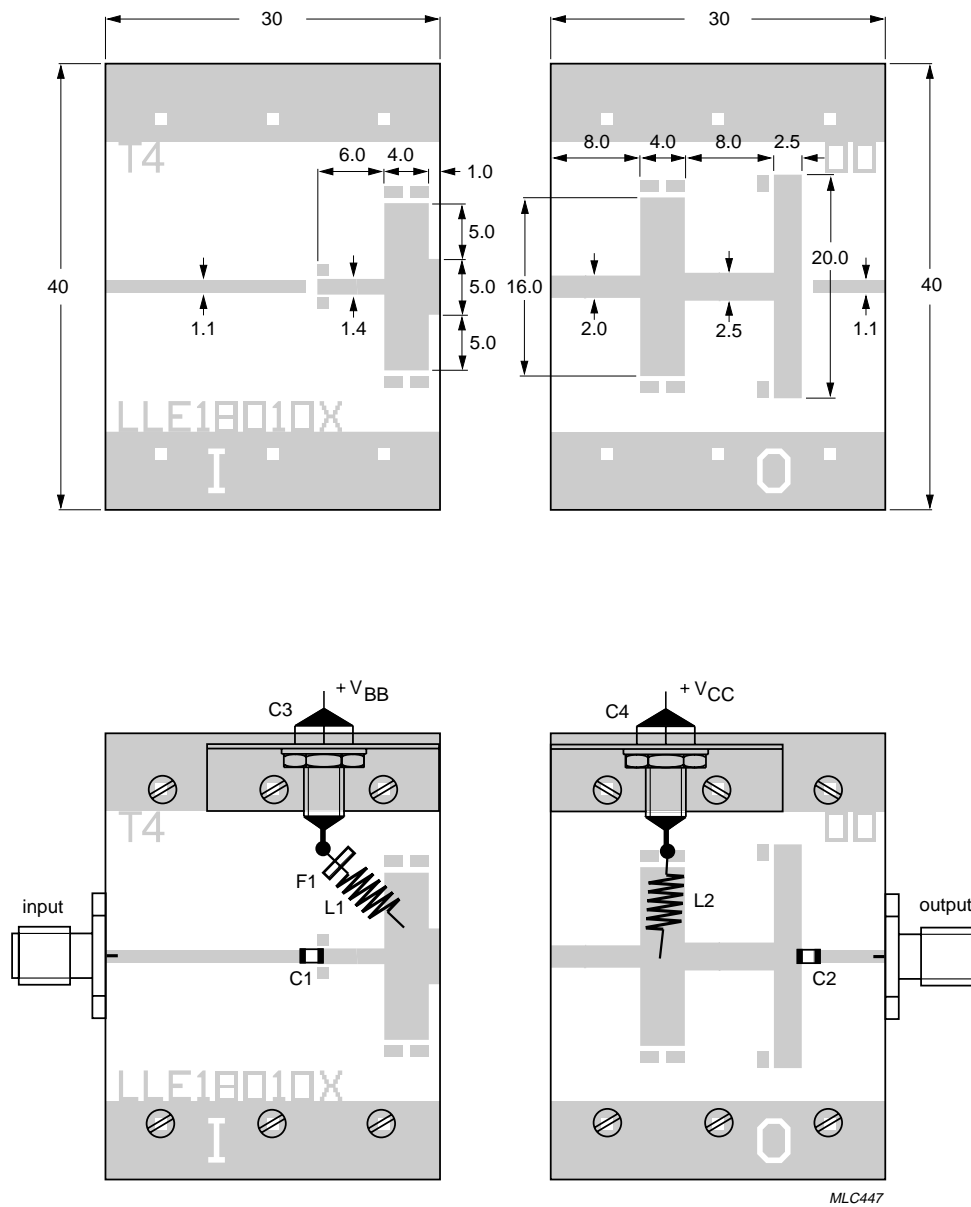
APPLICATION INFORMATION

Microwave performance up to $T_{mb} = 25\text{ °C}$ in a common emitter class AB amplifier.

MODE OF OPERATION	f (GHz)	V_{CE} (V)	I_{CQ} (mA)	P_{L1} (W)	G_{po} (dB)	η_c (%)	$Z_i; Z_L$ (Ω)
Class AB (CW)	1.85	24	10	≥ 1 typ. 1.5	≥ 8.5 typ. 10	typ. 40	see Figs 6 and 7
	1.65	24	10	typ. 2	typ. 11	typ. 47	see Figs 6 and 7

NPN microwave power transistor

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The test circuit is split into two independent halves, each being 30 x 40 mm in size.
 Dimensions in mm.
 Substrate: Teflon fibreglass.
 Thickness: 0.4 mm.
 Permittivity: $\epsilon_r = 2.55$.

Fig.3 Prematching test circuit board.

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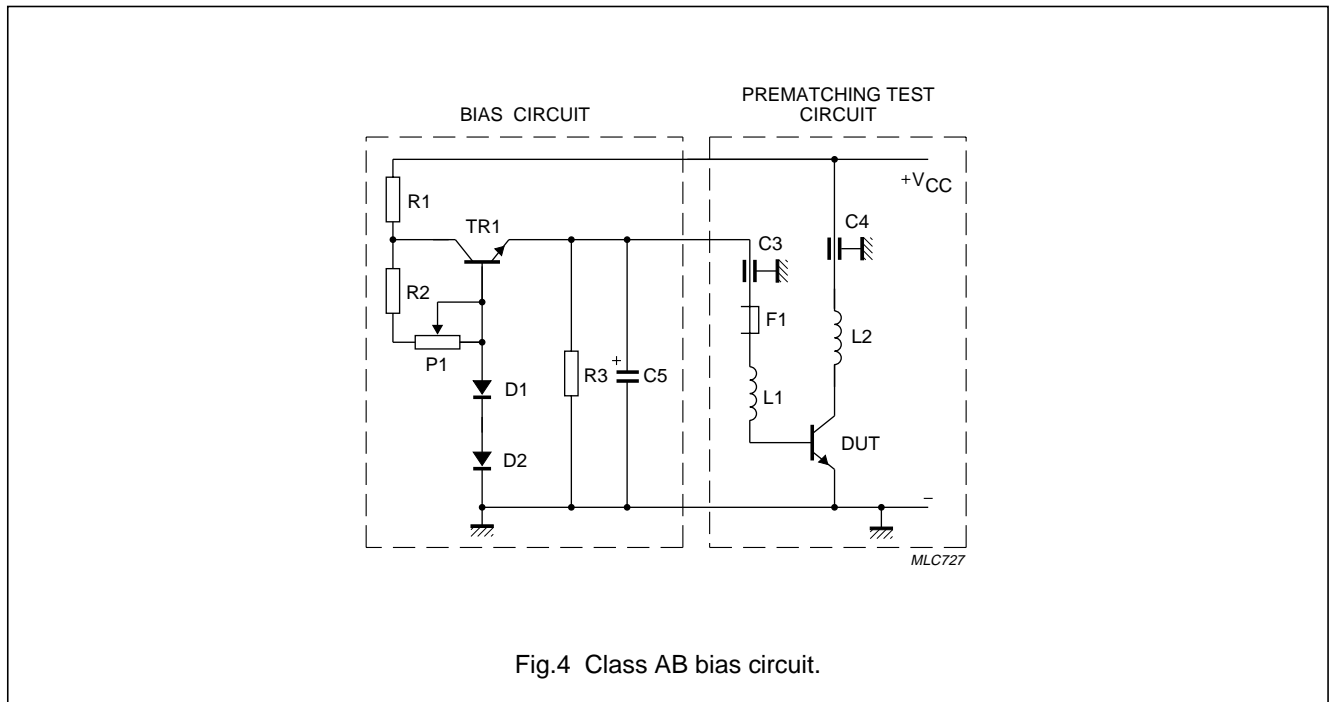


Fig.4 Class AB bias circuit.

List of components (see Figs 3 and 4)

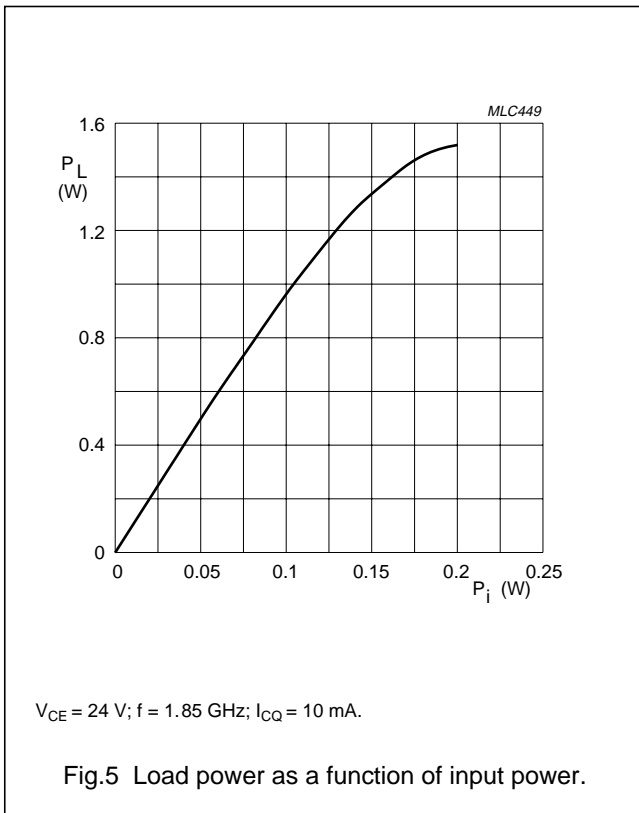
COMPONENT	DESCRIPTION	VALUE	ORDERING INFORMATION
TR1	transistor, BDT91 or equivalent		
C1, C2	DC blocking chip capacitor	100 pF	ATC 100A101kp
C3, C4	feedthrough bypass capacitor	1500 pF	Erie 1250-003
C5	electrolytic capacitor	10 μ F, >30 V	
D1	diode BY239 or equivalent; note 1		
D2	diode BY239 or equivalent; note 2		
L1	4 turns 0.5 mm copper wire; internal diameter = 2 mm		
L2	4 turns 0.5 mm copper wire; internal diameter = 2 mm		
P1	linear potentiometer	4.7 k Ω	
R1	resistor	100 Ω , 0.25 W	
R2	resistor	10 k Ω , 0.25 W	
R3	resistor	56 Ω , 0.25 W	
F1	ferrite bead		Philips tube, 12NC = 4330 030 43081 4.2 x 2.2 x 3.2 mm (4B1)

Notes

1. In thermal contact with TR1.
2. In thermal contact with DUT.

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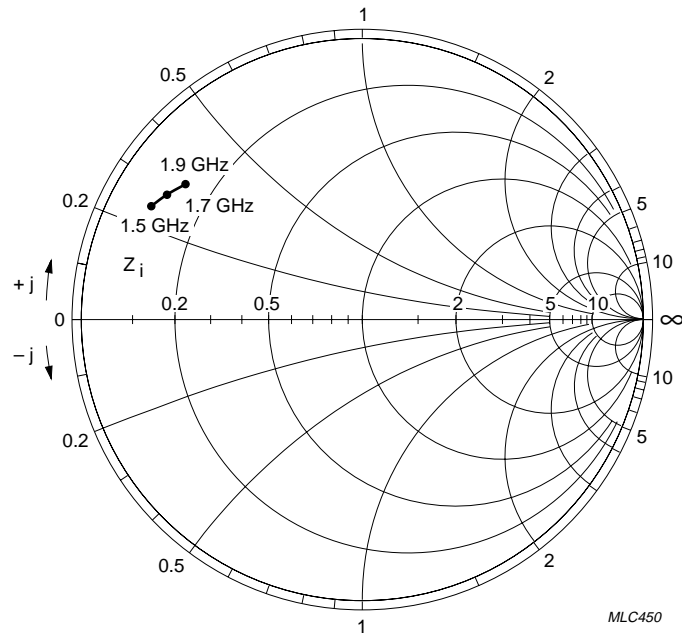
Input and optimum load impedances

$V_{CE} = 24\text{ V}; I_{CQ} = 50\text{ mA}$ (see Figs 6 and 7); typical values at $P_L = P_{L1}$.

f (GHz)	Z_i (Ω)	Z_L (Ω)
1.50	$4.7 + j12.0$	$8.2 + j21.7$
1.60	$5.0 + j13.0$	$7.3 + j20.5$
1.70	$5.5 + j14.0$	$6.5 + j19.0$
1.80	$6.0 + j15.2$	$6.2 + j17.5$
1.90	$6.7 + j16.5$	$5.9 + j16.0$

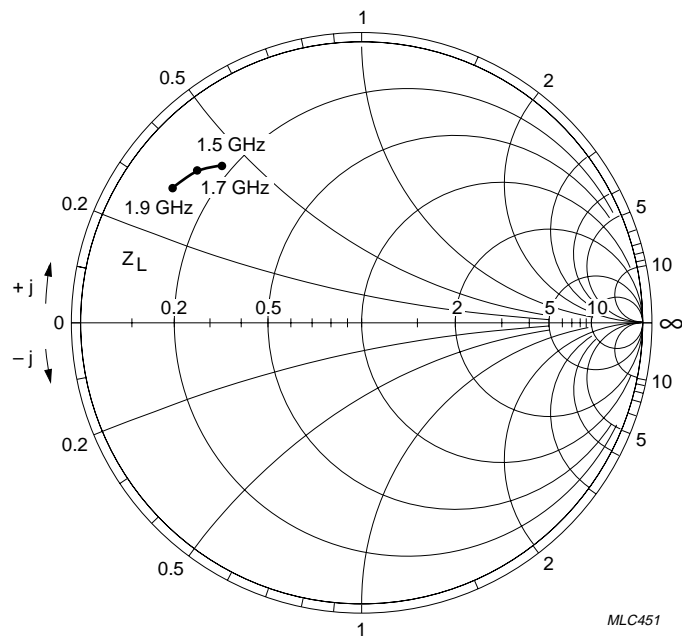
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$V_{CE} = 24 \text{ V}; Z_0 = 50 \Omega; I_{CQ} = 10 \text{ mA}.$

Fig.6 Input impedance as a function of frequency; typical values at $P_L = P_{L1}$.



$V_{CE} = 24 \text{ V}; Z_0 = 50 \Omega; I_{CQ} = 10 \text{ mA}.$

Fig.7 Optimum load impedance as a function of frequency; typical values at $P_L = P_{L1}$.

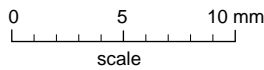
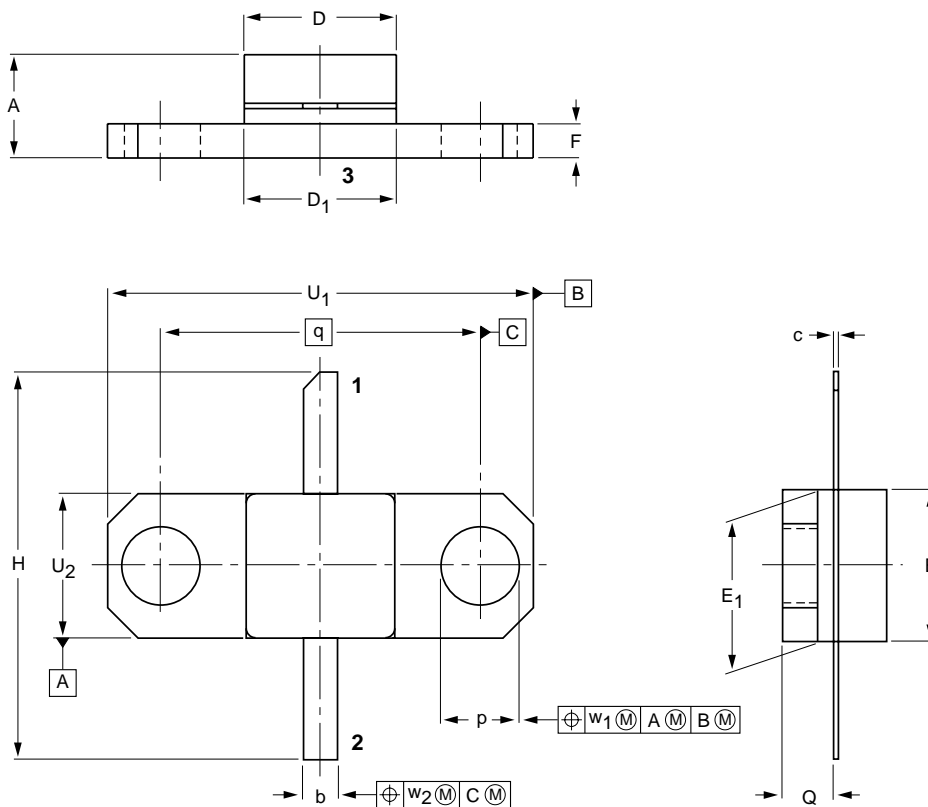
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PACKAGE OUTLINE

Flanged ceramic package; 2 mounting holes; 2 leads

SOT437A



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D ₁	E	E ₁	F	H	p	Q	q	U ₁	U ₂	w ₁	w ₂
mm	4.98 4.32	1.66 1.40	0.13 0.08	6.48 6.22	6.48 6.22	6.48 6.22	6.48 6.22	1.65 1.40	17.02 16.00	3.43 3.18	2.29 2.03	14.22	19.02 18.77	6.48 6.22	0.25	0.51
inches	0.196 0.170	0.065 0.055	0.005 0.003	0.255 0.245	0.255 0.245	0.255 0.245	0.255 0.245	0.065 0.055	0.67 0.63	0.135 0.125	0.90 0.80	0.560	0.749 0.739	0.255 0.245	0.010	0.020

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT437A					99-03-29

NPN microwave power transistor

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DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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Printed in The Netherlands

125002/00/02/pp12

Date of release: 1999 Apr 22

Document order number: 9397 750 05722

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